
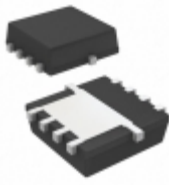
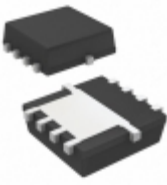

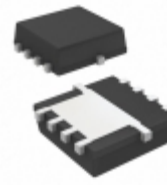
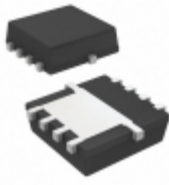



	<h2>SI7615ADN-T1-GE3</h2>
	<p><b>Hersteller-Teilenummer:</b> <a href="#">SI7615ADN-T1-GE3</a></p> <p><b>Hersteller / Marke:</b> <a href="#">Electro-Films (EFI) / Vishay</a></p> <p><b>Teil der Beschreibung:</b> MOSFET P-CH 20V 35A 1212-8S</p> <p><b>Datenblätter:</b>  <a href="#">SI7615ADN-T1-GE3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 51999 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	<a href="#">SI7615ADN-T1-GE3</a>
Hersteller	<a href="#">Electro-Films (EFI) / Vishay</a>
Beschreibung	MOSFET P-CH 20V 35A 1212-8S
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	51999 pcs Stock
Hersteller Standard Vorlaufzeit	32 Weeks
detaillierte Beschreibung	P-Channel 20V 35A (Tc) 3.7W (Ta), 52W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® 1212-8
Supplier Device-Gehäuse	PowerPAK® 1212-8
Verlustleistung (max)	3.7W (Ta), 52W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	35A (Tc)
Rds On (Max) @ Id, Vgs	4.4 mOhm @ 20A, 10V
VGS (th) (Max) @ Id	1.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	183nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	5590pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	2.5V, 10V
Vgs (Max)	±12V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7615ADN-T1-GE3TR

SI7615ADN-T1-GE3 ist neu im Original. Suche SI7615ADN-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7615ADN-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7615ADN-T1-GE3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>SI7615ADN-T1-GE3</b> Vishay / Siliconix MOSFET P-CH 20V 35A 1212-8S</p>	 <p><b>SI7613DN-T1-GE3</b> Vishay / Siliconix MOSFET P-CH 20V 35A 1212-8 PPAK</p>	 <p><b>SI7615CDN-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET P-CH 20V 35A POWERPAK1212</p>	 <p><b>SI7615CDN-T1-GE3</b> Vishay / Siliconix MOSFET P-CH 20V 35A 1212-8</p>
 <p><b>SI7613DN-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET P-CH 20V 35A 1212-8 PPAK</p>	 <p><b>SI7615DN-T1-E3</b> VISHAY SI7615DN-T1-E3 VISHAY</p>	 <p><b>SI7615ADN-T1-E3</b> VISHAY VISHAY PAK1212</p>	 <p><b>SI7615DN</b> SI SI7615DN SI</p>

heiße Teile

Mehr

⚙ SI7483DP-T1-GE3	↔ SI7485DP-T1-E3	➔ SI7485DP-T1-E3	D SI7485DP-T1-GE3	↔ SI7485DP-T1-GE3
⊣ SI7489DP	⚙ SI7489DP-T1-GE3	D SI7489DP-T1-GE3	➔ SI7491DP	↔ SI7491DP-T1-GE3
⚙ SI7491DP-T1-GE3	⊣ SI7501DN-T1-E3	⚙ SI7501DN-T1-E3	↔ SI7540ADP-T1-GE3	↔ SI7540ADP-T1-GE3
D SI7540DP-T1-E3	⚙ SI7540DP-T1-E3	⊣ SI7540DP-T1-GE3	⚙ SI7540DP-T1-GE3	↔ SI7606DN-T1-E3
➔ SI7606DN-T1-GE3	↔ SI7611DN-T1-GE3	⚙ SI7611DN-T1-GE3	⊣ SI7613DN-T1-GE3	↔ SI7613DN-T1-GE3
↔ SI7615ADN-T1-GE3	➔ SI7615DN	D SI7615DN-T1-E3	⚙ SI7615DN-T1-GE3	⊣ SI7615DN-T1-GE3
⚙ SI7617DN-T1-GE3	D SI7617DN-T1-GE3	➔ SI7619DN-T1-GE3	↔ SI7619DN-T1-GE3	↔ SI7621DN-T1-GE3
⊣ SI7621DN-T1-GE3	⚙ SI7625DN-T1-GE3	↔ SI7625DN-T1-GE3	➔ SI7629DN-T1	↔ SI7629DN-T1-GE3
⚙ SI7629DN-T1-GE3	⊣ SI7633DP-T1-GE3	⚙ SI7633DP-T1-GE3	D SI7634BDP	↔ SI7634BDP-T1-E3
↔ SI7634BDP-T1-E3	⚙ SI7634BDP-T1-GE3	⊣ SI7634BDP-T1-GE3	⚙ SI7634DP-T1-E3	↔ SI7634DP-T1-GE3

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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